

# Shashi Bala

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/12128477/publications.pdf>

Version: 2024-02-01

13  
papers

103  
citations

1478505

6  
h-index

1372567

10  
g-index

13  
all docs

13  
docs citations

13  
times ranked

61  
citing authors

#	ARTICLE	IF	CITATIONS
1	Parameter Variation Analysis of Dopingless and Junctionless Nanotube MOSFET. Silicon, 2022, 14, 5255-5263.	3.3	4
2	Study and Analysis of Advanced 3D Multi-Gate Junctionless Transistors. Silicon, 2022, 14, 1053-1067.	3.3	9
3	Design and Simulation Analysis of NWFET for Digital Application. Advances in Computer and Electrical Engineering Book Series, 2021, , 123-138.	0.3	1
4	Comparative Performance Analysis of Nanowire and Nanotube Field Effect Transistors. Advances in Computer and Electrical Engineering Book Series, 2021, , 54-70.	0.3	0
5	Improved Sensitivity of Dielectric Modulated Junctionless Transistor for Nanoscale Biosensor Design. Sensor Letters, 2020, 18, 328-333.	0.4	8
6	CNTFET-Based Memory Design. Advances in Computer and Electrical Engineering Book Series, 2020, , 16-36.	0.3	1
7	Design and performance analysis of low-power SRAM based on electrostatically doped tunnel CNTFETs. Journal of Computational Electronics, 2019, 18, 856-863.	2.5	17
8	Design and simulation of nanoscale double-gate TFET/tunnel CNTFET. Journal of Semiconductors, 2018, 39, 044001.	3.7	18
9	Design and analysis of electrostatic doped tunnel CNTFET for various process parameters variation. Superlattices and Microstructures, 2018, 124, 160-167.	3.1	27
10	Electrostatically doped tunnel CNTFET model for low-power VLSI circuit design. Journal of Computational Electronics, 2018, 17, 1528-1535.	2.5	11
11	Comparative Study and Analysis of CNTFET and Tunnel CNTFET. Journal of Nanoelectronics and Optoelectronics, 2018, 13, 324-330.	0.5	7
12	Comparative performance analysis of Carbon Nanotube and Si-Nanotube based Field effect Transistors. IOP Conference Series: Materials Science and Engineering, 0, 1033, 012028.	0.6	0
13	Silicon Material Based Tunnel FET for Controlling Ambipolar Current. Silicon, 0, , 1.	3.3	0